

BGR420

NPN Silicon RF Transistor With Bias Circuitry

Small Signal Discretes



Never stop thinking

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BGR420, NPN Silicon RF Transistor With Bias Circuitry

Revision History: 2008-06-06, Rev. 1.0

Prevision History: no previous version

Page	Subjects (major changes since last revision)

Trademarks

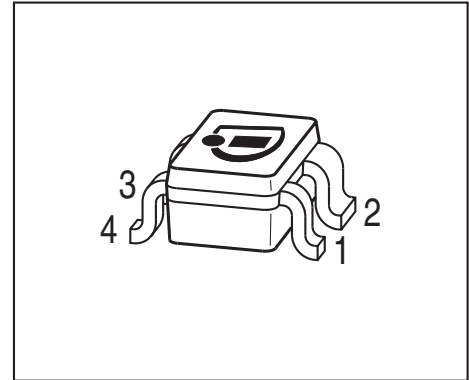
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1 NPN Silicon RF Transistor With Bias Circuitry*

Features

- Noise figure $NF = 1.5$ dB at 0.4 GHz
- Gain $S_{21} = 26$ dB at 0.4 GHz
- On chip bias circuitry, 13 mA bias current at $V_{CC} = 3.6$ V;
 $V_{BB} = 2.8$ V
- SIEGET® 25 GHz f_T -Line
- Pb-free (RoHS compliant) package

* Short term description



Applications

- LNAs

2 Description

The BGR420 is a monolithic silicon amplifier with a NPN silicon RF transistor and integrated resistors for biasing.

Type	Package	Marking
BGR420	SOT343	AWs

Note: **ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

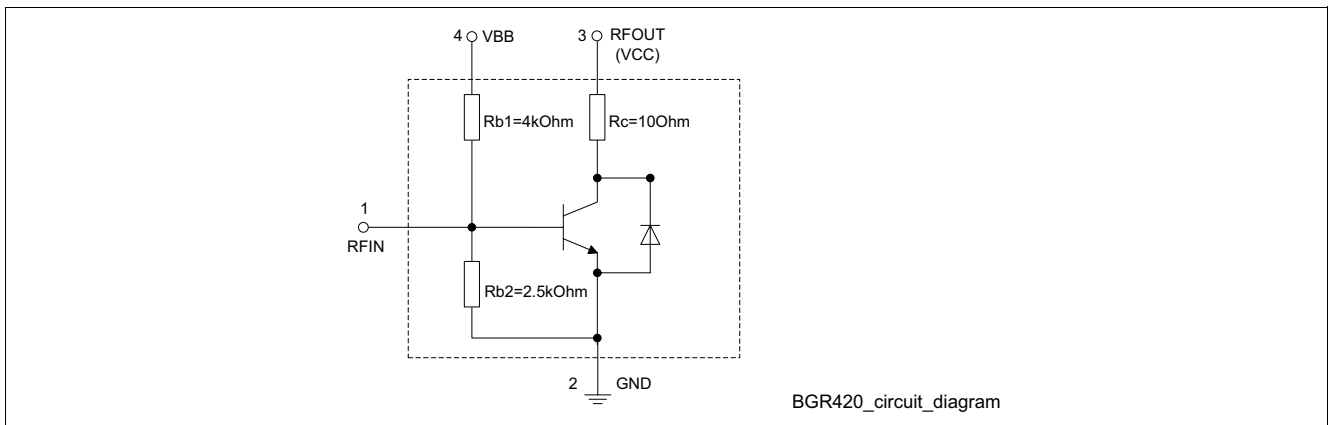


Figure 1 Circuit diagram

Note: Due to design there is an additional diode between emitter and collector, which does not affect normal operation for common emitter configuration.

Table 1 Pinning table

Pin	Function
1	RFIN
2	GND
3	RFOUT (VCC)
4	VBB

2.1 Maximum Ratings

Note: All Voltages refer to GND-node

Table 2 Maximum ratings

Parameter	Symbol	Value	Unit
Current at pin VCC	I_{CC}	25	mA
Voltage at pin VCC	V_{CC}	13	V
Current at pin VBB	I_{BB}	2.2	mA
Voltage at pin VBB	V_{BB}	8	V
Current at pin RFIN	I_{IN}	3	mA
Voltage at pin RFIN	V_{IN}	5	V
Total power dissipation ¹⁾ $T_S = 115\text{ °C}$	P_{tot}	120	mW
Operation junction temperature range	T_{jo}	-65... 150	°C
Storage junction temperature range	T_{jstg}	-65... 150	°C

1) T_S is measured on the emitter (GND) lead at the soldering point to the pcb

Note: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions even only for a short moment may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit. Absolute maximum ratings typically differ heavily from recommended operation conditions

2.2 Thermal Resistance

Table 3 Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 290	K/W

1) For calculation of R_{thJA} please refer to Application Note Thermal Resistance.

3 Electrical Characteristics

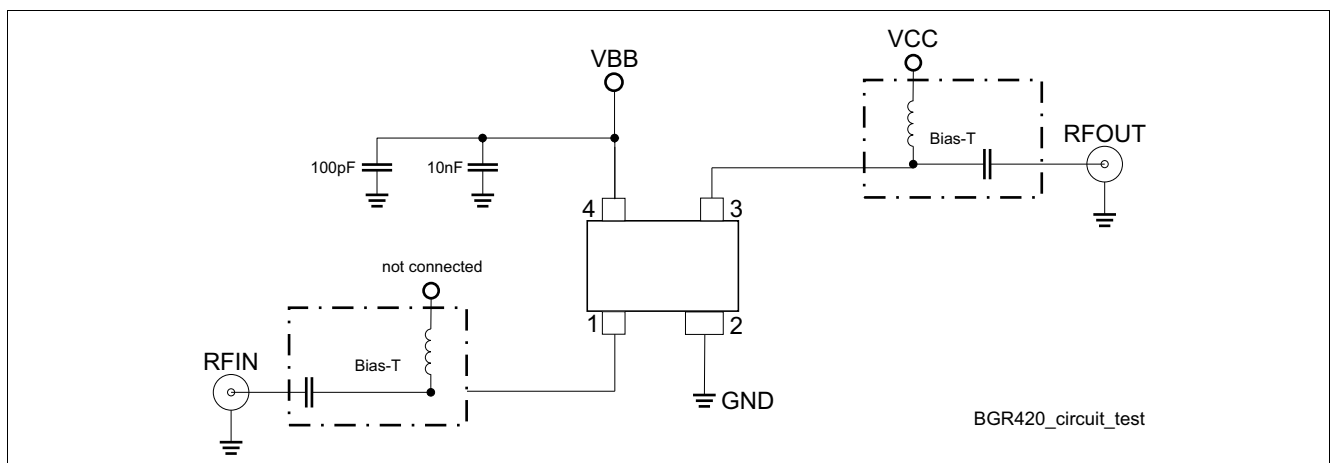
Table 4 DC characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
VCC-GND cutoff current	I_{CC}			10	μA	$V_{CC} = 13\text{ V}$, $I_{BB} = 0$, $V_{IN} = 0$
Current at pin VCC	I_{CC}	7	13	20	mA	$V_{BB} = 2.8\text{ V}$, $I_{IN} = 0$, $V_{CC} = 3.6\text{ V}$

**Table 5 AC characteristics (measured in test circuit [Figure 2](#); verified by random sampling)
 $T_A = 25\text{ }^\circ\text{C}$, $V_{BB} = 2.8\text{ V}$, $V_{CC} = 3.6\text{ V}$, $Z_0 = 50\text{ }\Omega$, unless otherwise specified**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Insertion power gain	S_{21}		26.0 15.5		dB	$f = 0.4\text{ GHz}$ $f = 1.8\text{ GHz}$
Reverse isolation	S_{12}		-32.5 -23.4		dB	$f = 0.4\text{ GHz}$ $f = 1.8\text{ GHz}$
Noise figure, $Z_S = Z_{\text{Sopt}}$	NF		1.5 1.7		dB	$f = 0.4\text{ GHz}$ $f = 1.8\text{ GHz}$
Third order intercept point at the output ¹⁾	OIP_3		21 23		dBm	$f = 0.4\text{ GHz}$ $f = 1.8\text{ GHz}$
1 dB compression point at the output	$OP_{-1\text{dB}}$		5.5 7.4		dBm	$f = 0.4\text{ GHz}$ $f = 1.8\text{ GHz}$
Return loss input	S_{11}		-7.3 -11		dB	$f = 0.4\text{ GHz}$ $f = 1.8\text{ GHz}$
Return loss output	S_{22}		-2.5 -9.5		dB	$f = 0.4\text{ GHz}$ $f = 1.8\text{ GHz}$

1) OIP_3 value depends on termination of all intermodulation frequency components. Termination used for this measurement is $50\text{ }\Omega$ from 0.1 MHz to 6 GHz.


Figure 2 BGR420 test circuit

4 Package Information

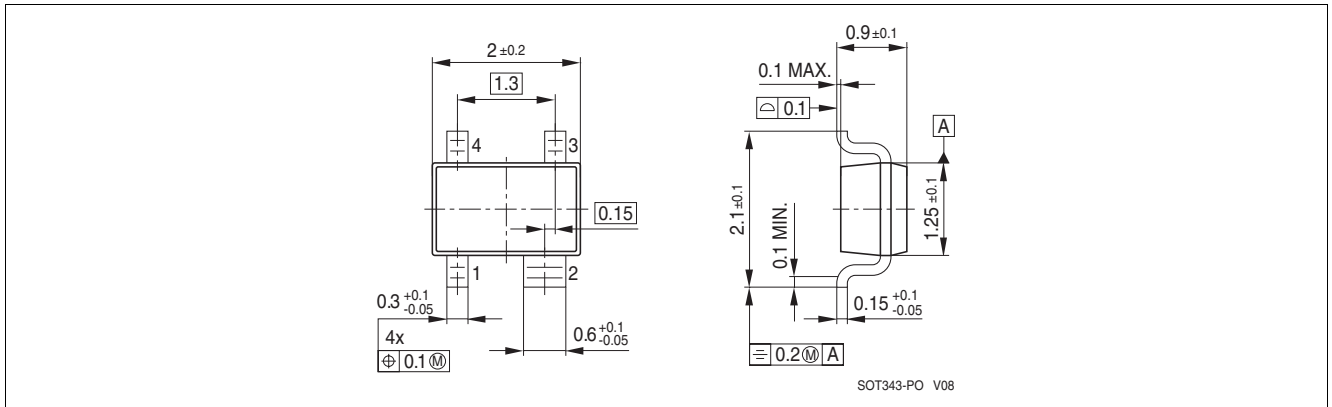


Figure 3 Package Outline SOT343

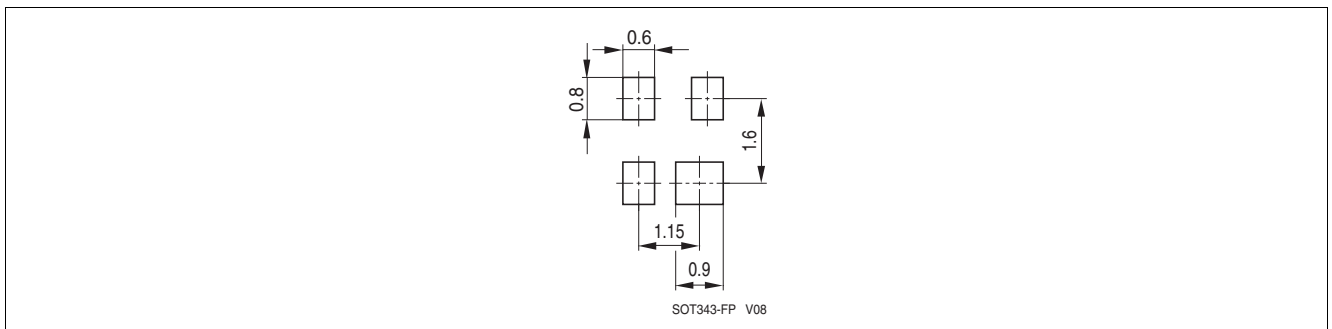


Figure 4 Footprint of SOT343

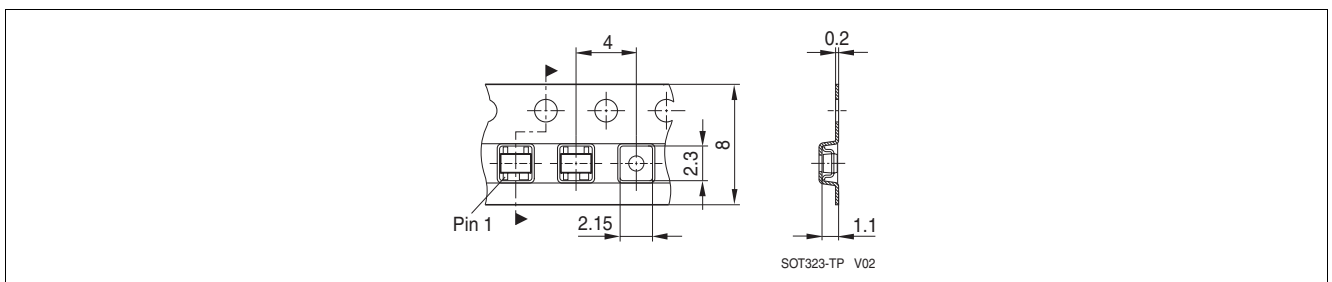


Figure 5 Tape of SOT343